

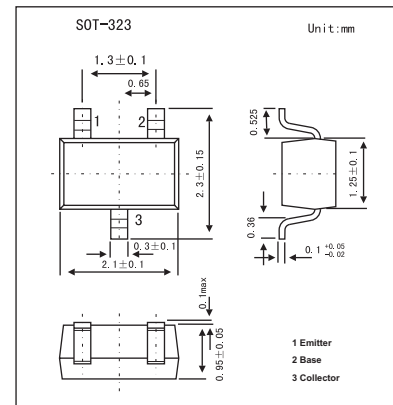
General Purpose Transistor

2SC4081

■ Features

- Low Cob.

Cob=2.0pF (Typ.)



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	7	V
Collector current	I _C	0.15	A
Collector power dissipation	P _C	0.2	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	BV _{CB0}	I _C =50μA	60			V
Collector-emitter voltage	BV _{CEO}	I _C =1mA	50			V
Emitter-base voltage	BV _{EBO}	I _E =50μA	7			V
Collector cutoff current	I _{CBO}	V _{CB} =60V			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} =7V			0.1	μA
Forward current transfer ratio	h _{FE}	V _{CE} =6V, I _C =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C /I _B =50mA/5mA			0.4	V
Transition frequency	f _T	V _{CE} =12V, I _E =2mA, f=100MHz		180		MHz
Output capacitance	C _{ob}	V _{CE} =12V, I _E =0A, f=1MHz		2	3.5	pF

■ hFE Classification

Marking	BQ	BR	BS
hFE	120~270	180~390	270~560